



**THE DATASHEET OF  
2N5401RLRAG**



# 2N5401

## Amplifier Transistors PNP Silicon

### Features

- These are Pb-Free Devices\*

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	$V_{CEO}$	150	Vdc
Collector – Base Voltage	$V_{CBO}$	160	Vdc
Emitter – Base Voltage	$V_{EBO}$	5.0	Vdc
Collector Current – Continuous	$I_C$	600	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.5 12	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

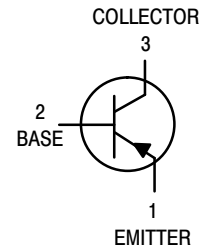
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

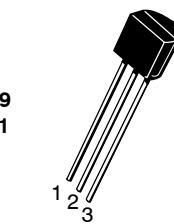


ON Semiconductor®

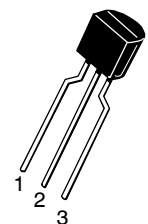
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TO-92  
CASE 29  
STYLE 1

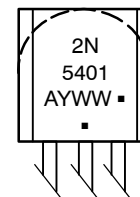


STRAIGHT LEAD  
BULK PACK



BENT LEAD  
TAPE & REEL  
AMMO PACK

### MARKING DIAGRAM



A = Assembly Location  
Y = Year  
WW = Work Week  
■ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## 2N5401

### ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Breakdown Voltage (Note 1) (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	150	–	V <sub>dc</sub>
Collector–Base Breakdown Voltage (I <sub>C</sub> = 100 μA <sub>dc</sub> , I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	160	–	V <sub>dc</sub>
Emitter–Base Breakdown Voltage (I <sub>E</sub> = 10 μA <sub>dc</sub> , I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	5.0	–	V <sub>dc</sub>
Collector Cutoff Current (V <sub>CB</sub> = 120 V <sub>dc</sub> , I <sub>E</sub> = 0) (V <sub>CB</sub> = 120 V <sub>dc</sub> , I <sub>E</sub> = 0, T <sub>A</sub> = 100°C)	I <sub>CBO</sub>	–	50	nA <sub>dc</sub> μA <sub>dc</sub>
Emitter Cutoff Current (V <sub>EB</sub> = 3.0 V <sub>dc</sub> , I <sub>C</sub> = 0)	I <sub>EBO</sub>	–	50	nA <sub>dc</sub>

### ON CHARACTERISTICS (Note 1)

DC Current Gain (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , V <sub>CE</sub> = 5.0 V <sub>dc</sub> ) (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 5.0 V <sub>dc</sub> ) (I <sub>C</sub> = 50 mA <sub>dc</sub> , V <sub>CE</sub> = 5.0 V <sub>dc</sub> )	h <sub>FE</sub>	50 60 50	– 240 –	–
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 10 mA <sub>dc</sub> , I <sub>B</sub> = 1.0 mA <sub>dc</sub> ) (I <sub>C</sub> = 50 mA <sub>dc</sub> , I <sub>B</sub> = 5.0 mA <sub>dc</sub> )	V <sub>CE(sat)</sub>	– –	0.2 0.5	V <sub>dc</sub>
Base–Emitter Saturation Voltage (I <sub>C</sub> = 10 mA <sub>dc</sub> , I <sub>B</sub> = 1.0 mA <sub>dc</sub> ) (I <sub>C</sub> = 50 mA <sub>dc</sub> , I <sub>B</sub> = 5.0 mA <sub>dc</sub> )	V <sub>BE(sat)</sub>	– –	1.0 1.0	V <sub>dc</sub>

### SMALL-SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> , f = 100 MHz)	f <sub>T</sub>	100	300	MHz
Output Capacitance (V <sub>CB</sub> = 10 V <sub>dc</sub> , I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	–	6.0	pF
Small–Signal Current Gain (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , V <sub>CE</sub> = 10 V <sub>dc</sub> , f = 1.0 kHz)	h <sub>fe</sub>	40	200	–
Noise Figure (I <sub>C</sub> = 250 μA <sub>dc</sub> , V <sub>CE</sub> = 5.0 V <sub>dc</sub> , R <sub>S</sub> = 1.0 kΩ, f = 1.0 kHz)	NF	–	8.0	dB

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

### ORDERING INFORMATION

Device	Package	Shipping†
2N5401G	TO–92 (Pb–Free)	5000 Unit / Bulk
2N5401RLRAG	TO–92 (Pb–Free)	2000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# 2N5401

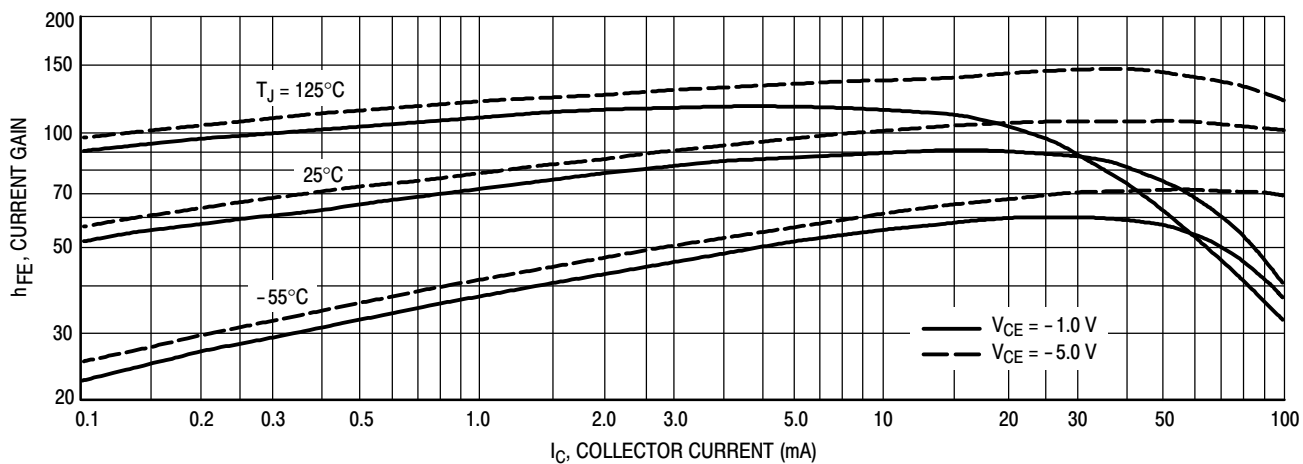


Figure 1. DC Current Gain

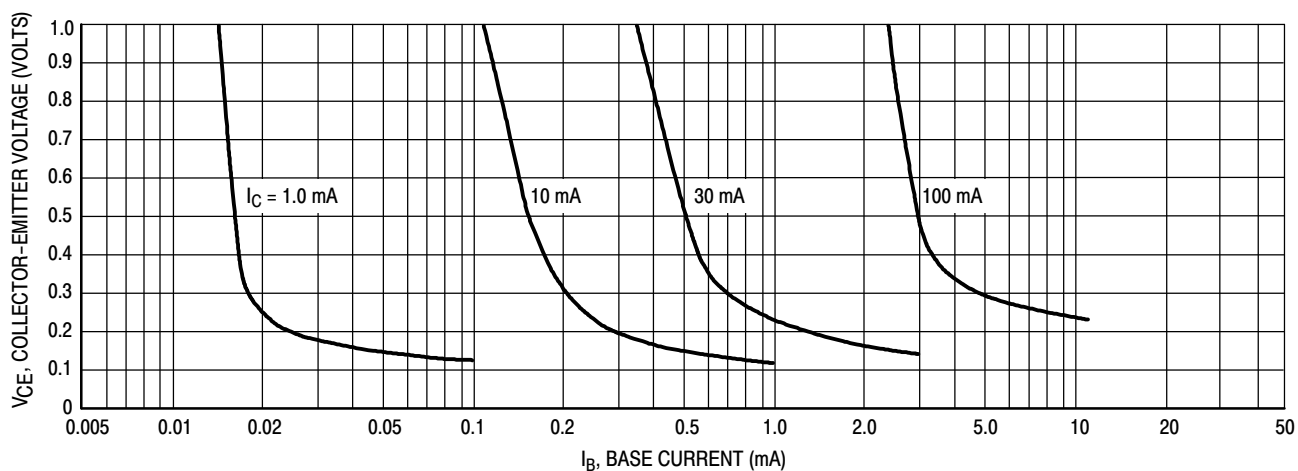


Figure 2. Collector Saturation Region

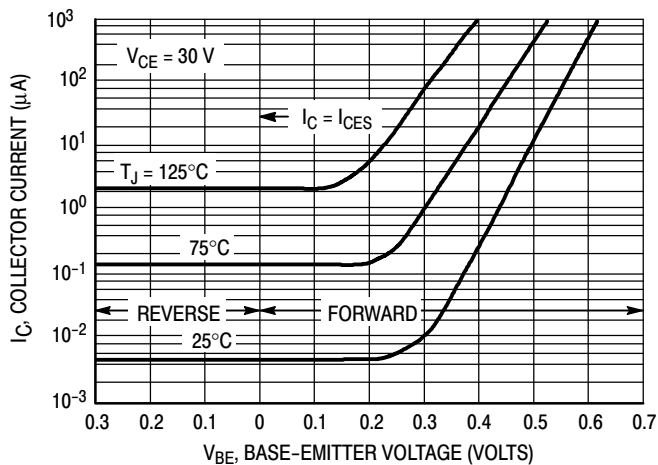


Figure 3. Collector Cut-Off Region

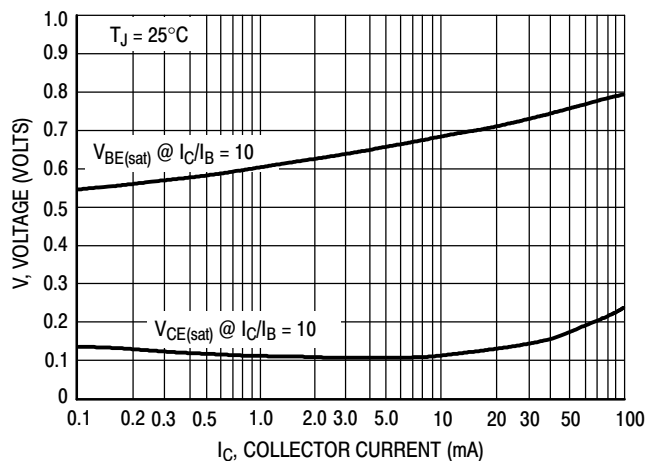


Figure 4. "On" Voltages

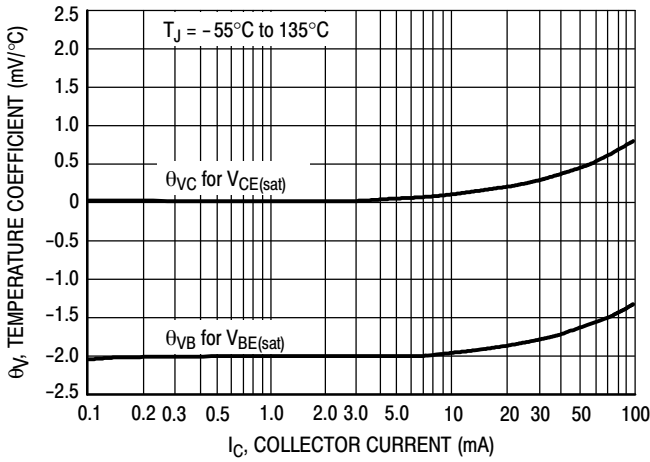
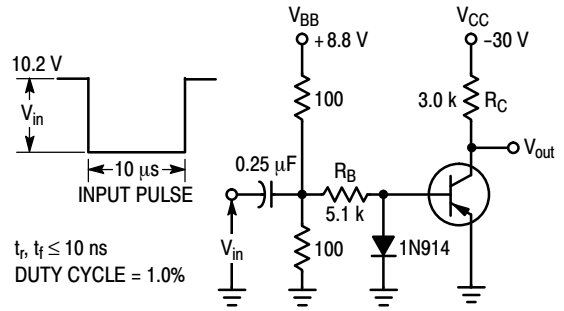


Figure 5. Temperature Coefficients



Values Shown are for  $I_C @ 10 \text{ mA}$

Figure 6. Switching Time Test Circuit

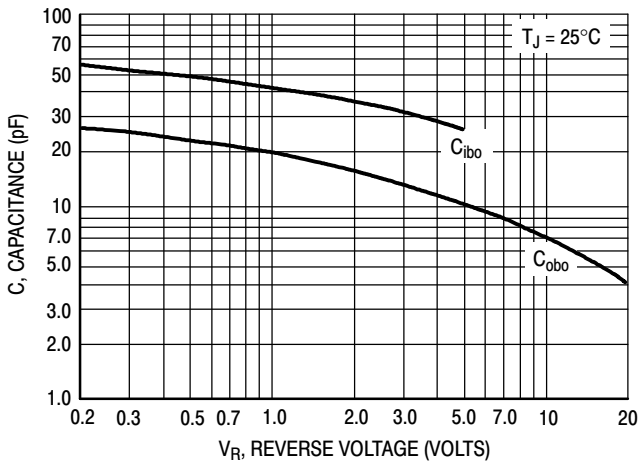


Figure 7. Capacitances

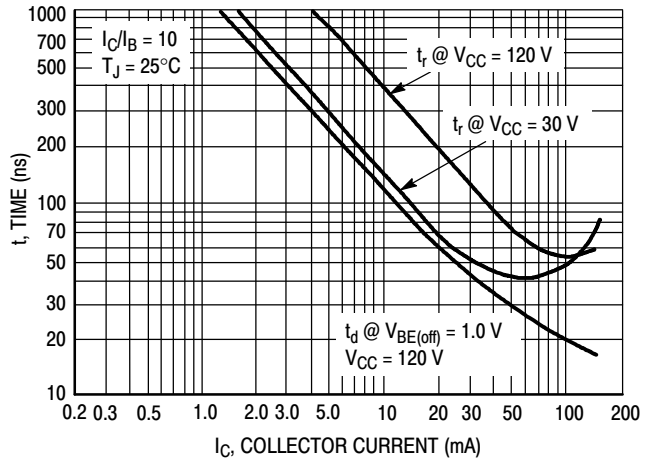


Figure 8. Turn-On Time

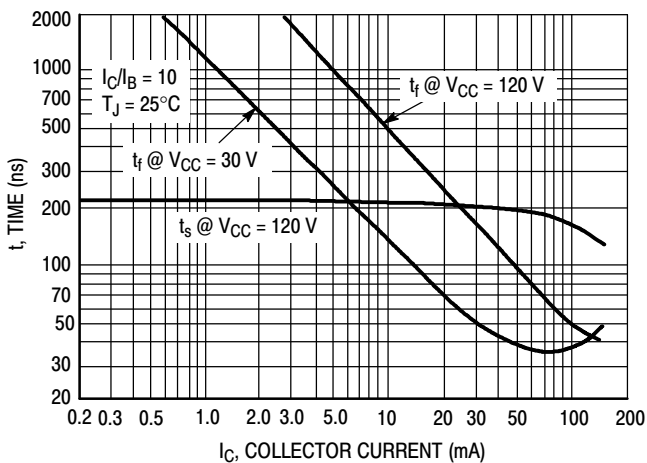


Figure 9. Turn-Off Time

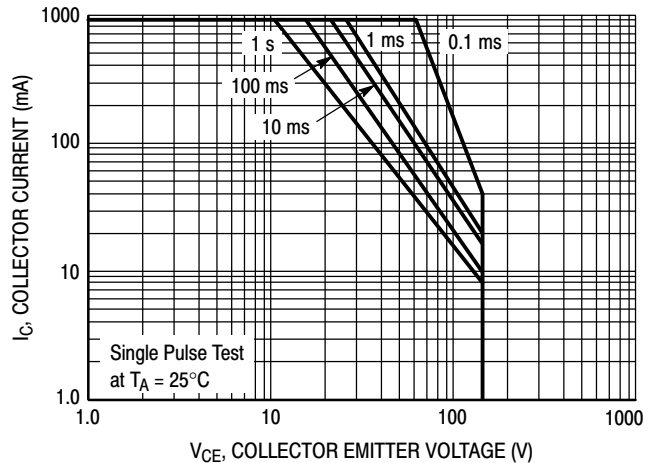
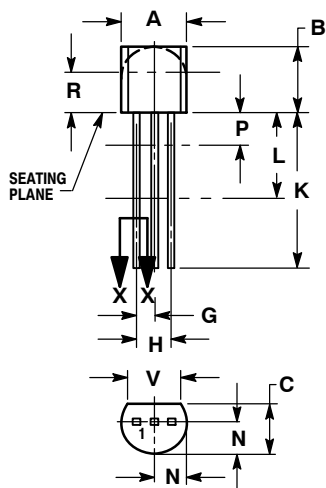


Figure 10. Safe Operating Area

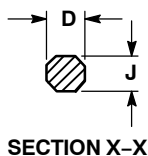
# 2N5401

## PACKAGE DIMENSIONS

TO-92 (TO-226)  
CASE 29-11  
ISSUE AM



STRAIGHT LEAD  
BULK PACK

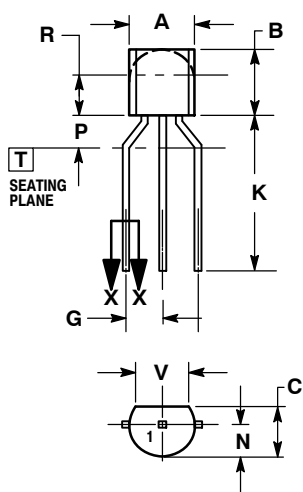


SECTION X-X

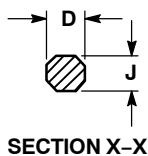
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---



BENT LEAD  
TAPE & REEL  
AMMO PACK



SECTION X-X

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	MILLIMETERS	
	MIN	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	0.40	0.54
G	2.40	2.80
J	0.39	0.50
K	12.70	---
N	2.04	2.66
P	1.50	4.00
R	2.93	---
V	3.43	---

STYLE 1:

1. EMITTER
2. BASE
3. COLLECTOR

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